



STD2NC60

N-CHANNEL 600V - 3.3Ω - 2A DPAK / IPAK

PowerMesh™ II MOSFET

| TYPE | V _{DSS} | R _{DS(on)} | I _D |
|----------|------------------|---------------------|----------------|
| STD2NC60 | 600V | < 3.6Ω | 2A |

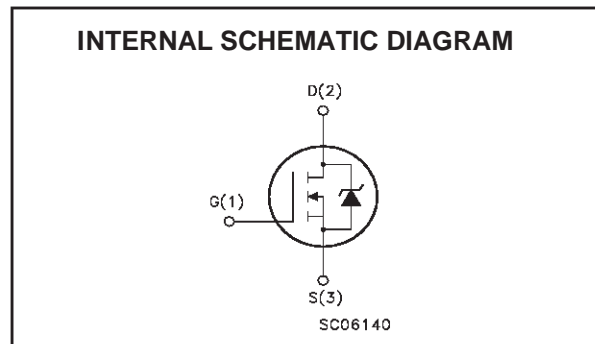
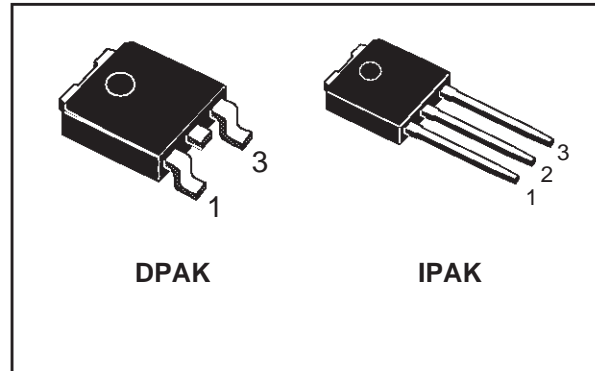
- TYPICAL R_{DS(on)} = 3.3Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The PowerMESH™ II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVERS



ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
|---------------------|--|------------|------|
| V _{DS} | Drain-source Voltage (V _{GS} = 0) | 600 | V |
| V _{DGR} | Drain-gate Voltage (R _{GS} = 20 kΩ) | 600 | V |
| V _{GS} | Gate- source Voltage | ±30 | V |
| I _D | Drain Current (continuous) at T _C = 25°C | 2 | A |
| I _D | Drain Current (continuous) at T _C = 100°C | 1.3 | A |
| I _{DM} (●) | Drain Current (pulsed) | 8 | A |
| P _{TOT} | Total Dissipation at T _C = 25°C | 60 | W |
| | Derating Factor | 0.48 | W/°C |
| dv/dt(1) | Peak Diode Recovery voltage slope | 4 | V/ns |
| T _{stg} | Storage Temperature | -65 to 150 | °C |
| T _j | Max. Operating Junction Temperature | 150 | °C |

(●)Pulse width limited by safe operating area

(1)I_{SD} ≤ 2A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{I(BR)DSS}, T_j ≤ T_{JMAX}.

STD2NC60

THERMAL DATA

| | | | |
|----------------|--|-----|------|
| Rthj-case | Thermal Resistance Junction-case Max | 2 | °C/W |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 100 | °C/W |
| T _l | Maximum Lead Temperature For Soldering Purpose | 275 | °C |

AVALANCHE CHARACTERISTICS

| Symbol | Parameter | Max Value | Unit |
|-----------------|--|-----------|------|
| I _{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max) | 2 | A |
| E _{AS} | Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V) | 80 | mJ |

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|----------------------|---|---|------|------|---------|----------|
| V _{(BR)DSS} | Drain-source Breakdown Voltage | I _D = 250 μA, V _{GS} = 0 | 600 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C | | | 1 50 | μA μA |
| I _{GSS} | Gate-body Leakage Current (V _{DS} = 0) | V _{GS} = ±30V | | | ±100 | nA |

ON (1)

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|-----------------------------------|--|------|------|------|------|
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} = V _{GS} , I _D = 250μA | 2 | 3 | 4 | V |
| R _{DS(on)} | Static Drain-source On Resistance | V _{GS} = 10V, I _D = 1.5 A | | 3.3 | 3.6 | Ω |
| I _{D(on)} | On State Drain Current | V _{DS} > I _{D(on)} × R _{DS(on)max} , V _{GS} = 10V | 2 | | | A |

DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------------|------------------------------|--|------|------|------|------|
| g _{fs} (1) | Forward Transconductance | V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 1.5A | 1.2 | 2 | | S |
| C _{iss} | Input Capacitance | V _{DS} = 25V, f = 1 MHz, V _{GS} = 0 | | 400 | | pF |
| C _{oss} | Output Capacitance | | | 57 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 7 | | pF |

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-------------|--------------------|--|------|------|------|------|
| $t_{d(on)}$ | Turn-on Delay Time | $V_{DD} = 300V, I_D = 1.5A$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 3) | | 13 | | ns |
| t_r | Rise Time | | | 9 | | ns |
| Q_g | Total Gate Charge | $V_{DD} = 480V, I_D = 3A,$ $V_{GS} = 10V$ | | 15 | 22 | nC |
| Q_{gs} | Gate-Source Charge | | | 6.2 | | nC |
| Q_{gd} | Gate-Drain Charge | | | 5.6 | | nC |

SWITCHING OFF

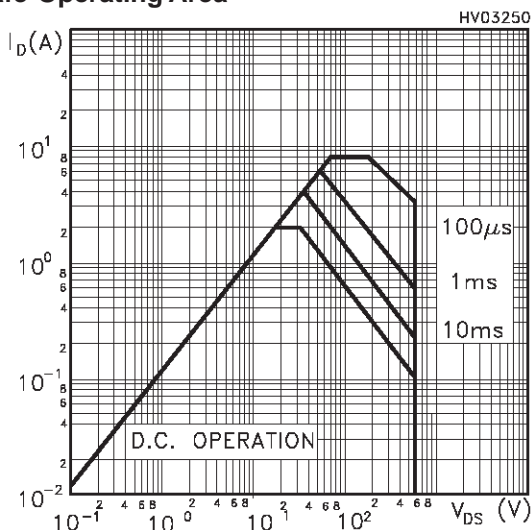
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------|---|------|------|------|------|
| $t_{r(Voff)}$ | Off-voltage Rise Time | $V_{DD} = 480V, I_D = 3A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see test circuit, Figure 5) | | 11 | | ns |
| t_f | Fall Time | | | 13 | | ns |
| t_c | Cross-over Time | | | 18 | | ns |

SOURCE DRAIN DIODE

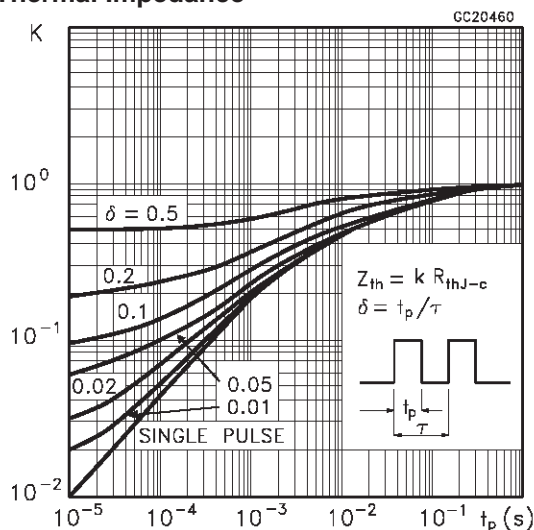
| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|-------------------------------|--|------|------|------|---------|
| I_{SD} | Source-drain Current | | | | 2 | A |
| $I_{SDM} (2)$ | Source-drain Current (pulsed) | | | | 8 | A |
| $V_{SD} (1)$ | Forward On Voltage | $I_{SD} = 3A, V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} | Reverse Recovery Time | $I_{SD} = 3A, di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 150^\circ C$ (see test circuit, Figure 5) | | 500 | | ns |
| Q_{rr} | Reverse Recovery Charge | | | 2.1 | | μC |
| I_{RRM} | Reverse Recovery Current | | | 8.5 | | A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

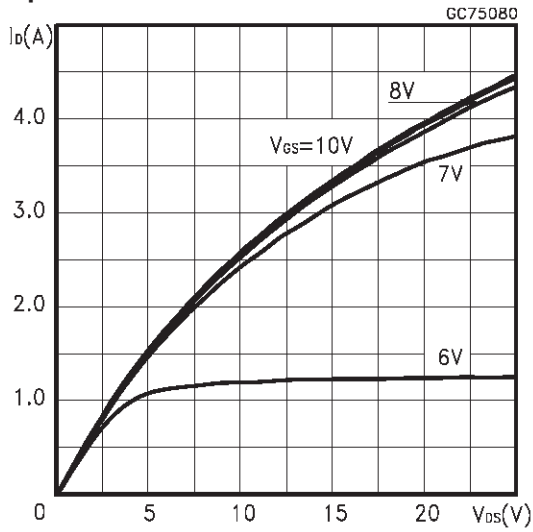
Safe Operating Area



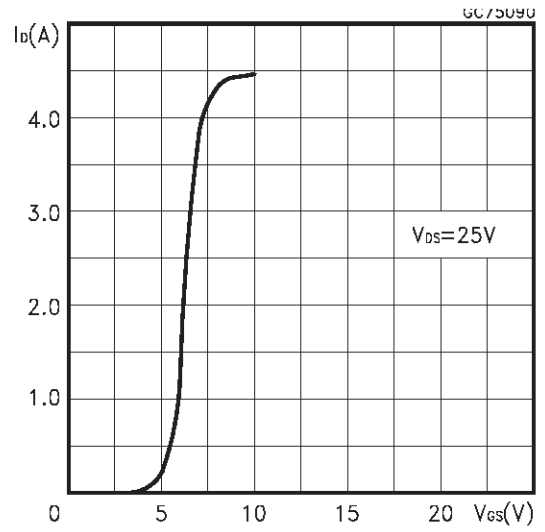
Thermal Impedance



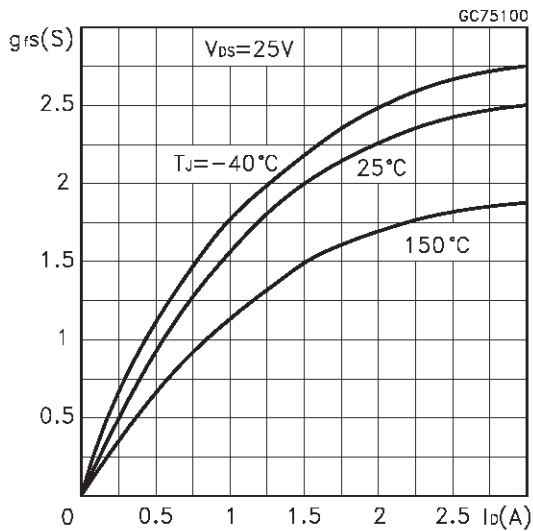
Output Characteristics



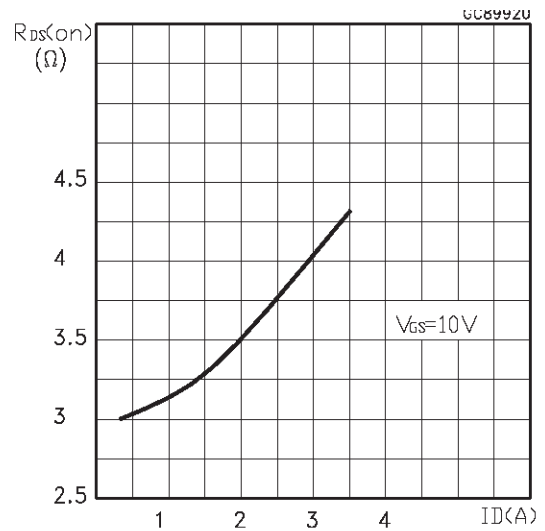
Transfer Characteristics



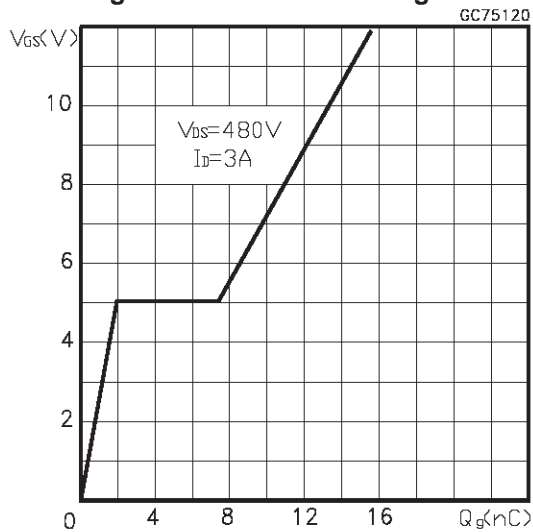
Transconductance



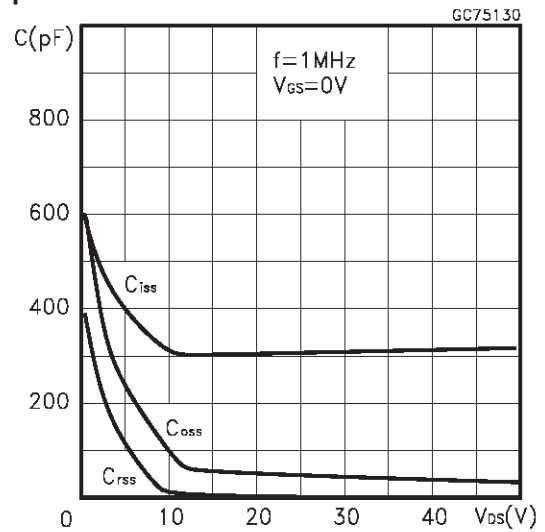
Static Drain-Source On Resistance



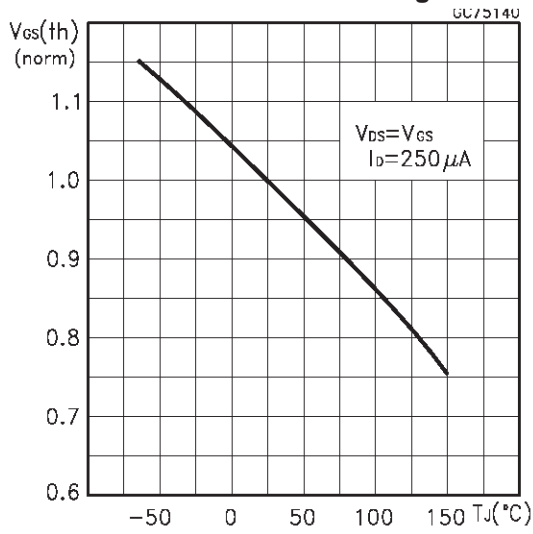
Gate Charge vs Gate-source Voltage



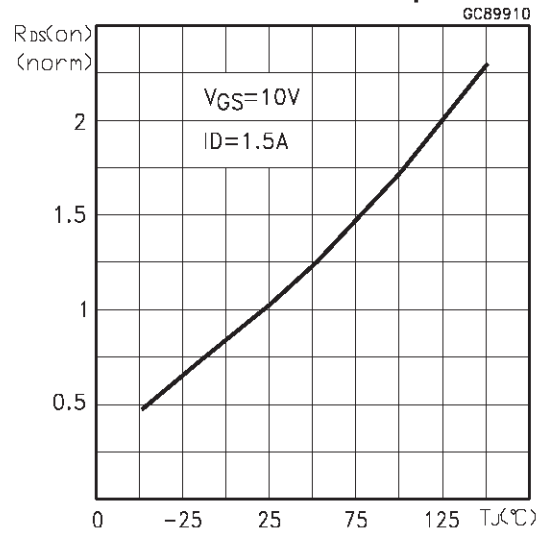
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

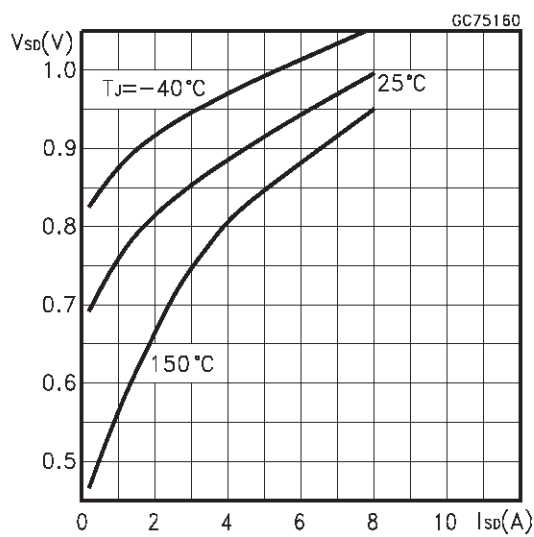


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform

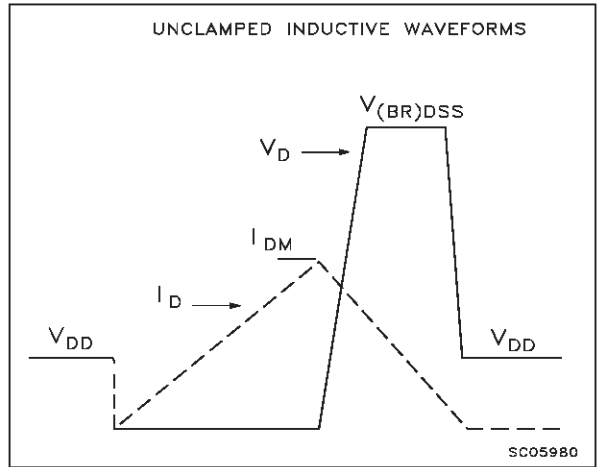


Fig. 3: Switching Times Test Circuits For Resistive Load

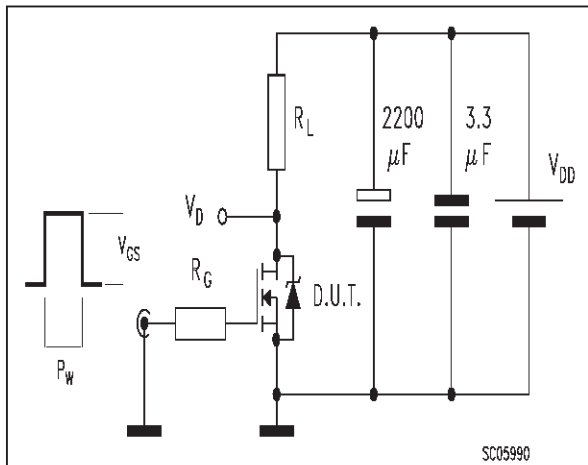


Fig. 4: Gate Charge test Circuit

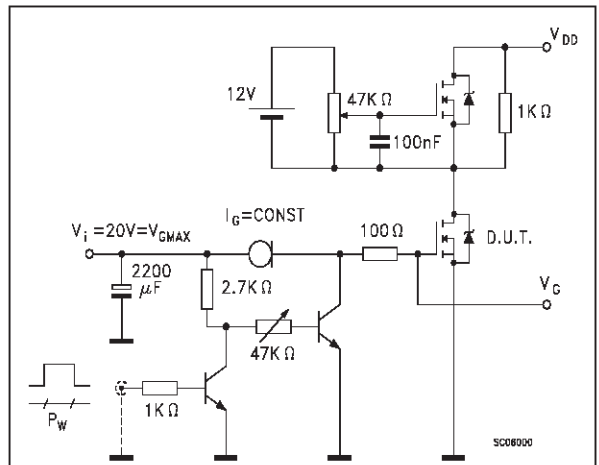
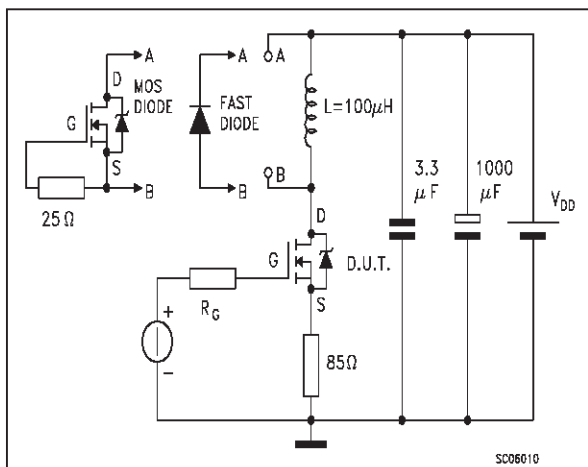
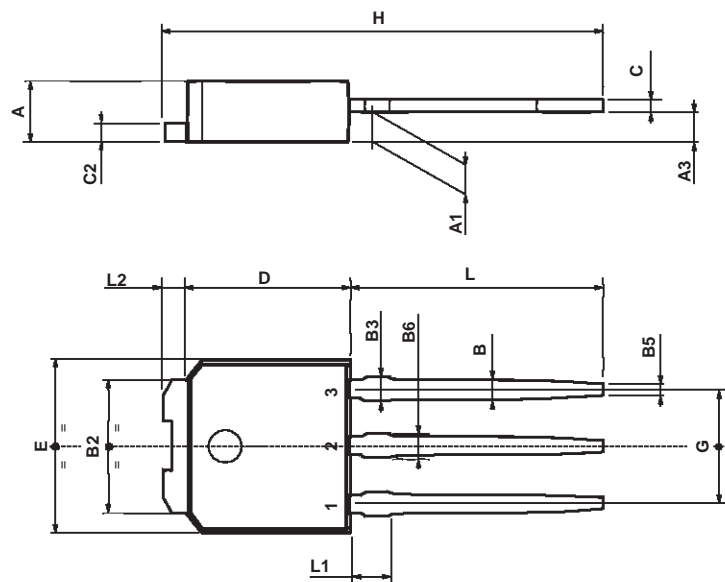


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-251 (IPAK) MECHANICAL DATA

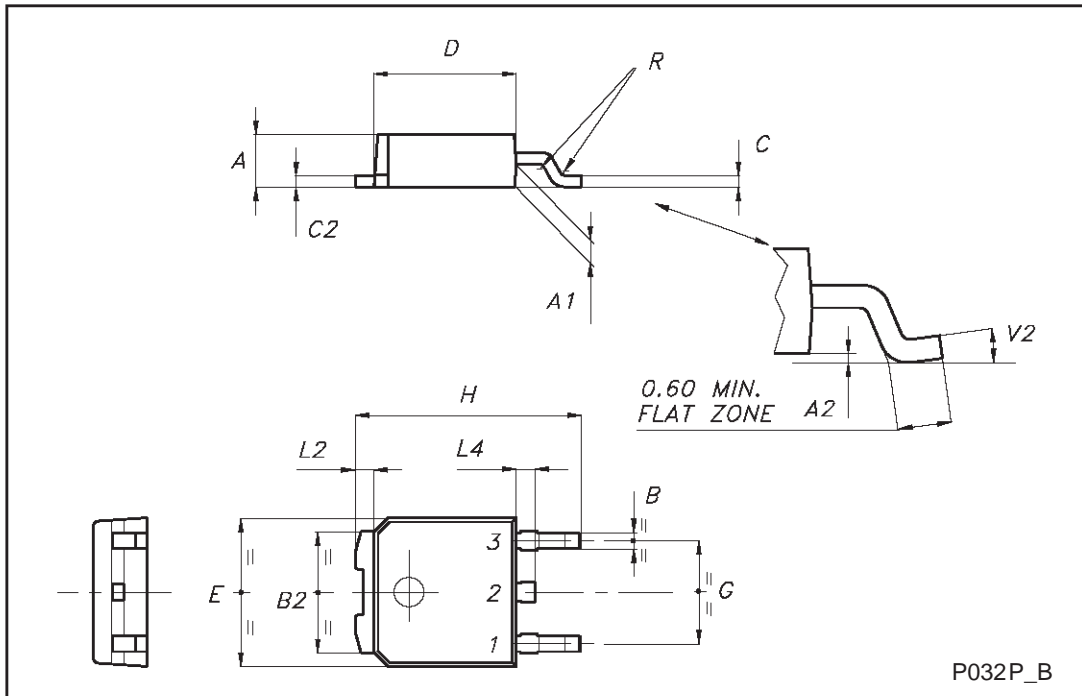
| DIM. | mm | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.2 | | 2.4 | 0.086 | | 0.094 |
| A1 | 0.9 | | 1.1 | 0.035 | | 0.043 |
| A3 | 0.7 | | 1.3 | 0.027 | | 0.051 |
| B | 0.64 | | 0.9 | 0.025 | | 0.031 |
| B2 | 5.2 | | 5.4 | 0.204 | | 0.212 |
| B3 | | | 0.85 | | | 0.033 |
| B5 | | 0.3 | | | 0.012 | |
| B6 | | | 0.95 | | | 0.037 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 0.48 | | 0.6 | 0.019 | | 0.023 |
| D | 6 | | 6.2 | 0.236 | | 0.244 |
| E | 6.4 | | 6.6 | 0.252 | | 0.260 |
| G | 4.4 | | 4.6 | 0.173 | | 0.181 |
| H | 15.9 | | 16.3 | 0.626 | | 0.641 |
| L | 9 | | 9.4 | 0.354 | | 0.370 |
| L1 | 0.8 | | 1.2 | 0.031 | | 0.047 |
| L2 | | 0.8 | 1 | | 0.031 | 0.039 |



0068771-E

TO-252 (DPAK) MECHANICAL DATA

| DIM. | mm | | | inch | | |
|------|------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 2.20 | | 2.40 | 0.087 | | 0.094 |
| A1 | 0.90 | | 1.10 | 0.035 | | 0.043 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.64 | | 0.90 | 0.025 | | 0.035 |
| B2 | 5.20 | | 5.40 | 0.204 | | 0.213 |
| C | 0.45 | | 0.60 | 0.018 | | 0.024 |
| C2 | 0.48 | | 0.60 | 0.019 | | 0.024 |
| D | 6.00 | | 6.20 | 0.236 | | 0.244 |
| E | 6.40 | | 6.60 | 0.252 | | 0.260 |
| G | 4.40 | | 4.60 | 0.173 | | 0.181 |
| H | 9.35 | | 10.10 | 0.368 | | 0.398 |
| L2 | | 0.8 | | | 0.031 | |
| L4 | 0.60 | | 1.00 | 0.024 | | 0.039 |
| V2 | 0° | | 8° | 0° | | 0° |



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